

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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HALL

Applicant: Tews, *et al.*

Attorney Docket: 00P9031US

Filed: November 16, 2000 ✓


Examiner: Chen, Jack S.J.

Serial No.: 09/714,356 ✓

Art Unit: 2813

Title: Nitrogen Implantation Using a Shadow Effect to Control Gate Oxide Thickness in DRAM Semiconductor

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

MAILING CERTIFICATE	
I hereby certify that this correspondence and all attached documentation is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P. O. Box 1450, Alexandria, Va. 22313-1450.	
 Julie Russell	Date: <u>August 12, 2003</u>

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant wishes to bring to the attention of the U.S. Patent and Trademark Office the information noted on the enclosed Form PTO/SB/08A which may be considered material to the examination of the above identified application.

This Information Disclosure Statement is submitted under 37 C.F.R. §1.97(c) together with a \$180.00 fee under 37 C.F.R. §1.17(p) after the C.F.R. §1.97(b) time period, but before final action or notice of allowance, whichever occurs first.

Please charge the required fee of \$180.00 and any additional amount, or credit any overpayment to Deposit Acct. No 50-1065 of the below mentioned firm.

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Respectfully submitted,



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